

(2) 参考

あくまでも参考であり、貨物等省令第6条第十七号ミとの一致を示すものではない。

〈米 EAR の規制リスト〉

3B993.q. Inspection and metrology equipment as follows:

3B993.q.1. Patterned wafer defect metrology or patterned wafer defect inspection equipment, designed or modified to accept wafers greater than or equal to 300 mm in diameter, and having all of the following:

3B993.q.1.a. Designed or modified to detect defects having a size equal to or less than 21 nm; and

3B993.q.1.b. Having any of the following:

3B993.q.1.b.1. A light source with an optical wavelength less than 400 nm;

3B993.q.1.b.2. An electron-beam source with a resolution less (better) than or equal to 1.65 nm;

3B993.q.1.b.3. A Cold Field Emission (CFE) electron-beam source; or

3B993.q.1.b.4. Two or more electron-beam sources.

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〈米 EAR の規制リスト〉

3B993.q.2. Metrology equipment as follows:

3B993.q.2.a. Stand-alone equipment designed to measure wafer shape parameters prior to lithography exposure and utilize measurements to improve overlay or focus of a deep ultraviolet (DUV) lithography system having an immersion lens having a numerical aperture more than 1.3 or an Extreme Ultraviolet lithography (EUV) system; or

3B993.q.2.b. Metrology equipment designed to measure focus or overlay after resist development or after etch on product wafers using image-based overlay or diffraction-based measurements techniques, with an overlay measurement accuracy less (better) than or equal to 0.5 nm having any of the following:

3B993.q.2.b.1. designed for integration to a 'track'; or

3B993.q.2.b.2. 'fast wavelength switching functionality';

Technical Notes:

1. *For the purposes of 3B993.q.2, a 'track' is equipment designed for coating and developing photoresist formulated for lithography.*

2. *For the purposes of 3B993.q.2, 'fast wavelength switching functionality' is defined as having the ability the change the measurement wavelength and acquire a measurement in less than 25 ms.*